

#### **60V DUAL PNP SMALL SIGNAL TRANSISTOR IN SOT-563**

#### **Features**

- $BV_{ceo} > -60V$
- I<sub>C</sub> = -600mA Collector Current
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMDT2222V
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.003 grams (Approximate)

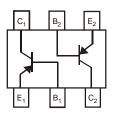
SOT-563



Top View



**Bottom View** 



**Device Schematic** 

#### **Ordering Information** (Note 4)

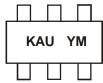
Part Number	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel
MMDT2907V-7	Active	AEC-Q101	KAU	7	8mm	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

SOT-563



KAU = Product Type Marking Code YM = Date Code Marking Y = Year (ex: R = 2004)M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н		J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	Ic	-600	mA

# Thermal Characteristics

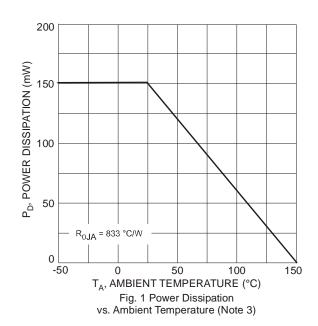
Total Power Dissipation (Note 5)	$P_{D}$	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

## **Thermal Characteristics and Derating Information**



 <sup>5.</sup> For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-60		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage ( Note 7)		-60	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current	1		-10	nA	$V_{CB} = -50V, I_{E} = 0$
Conector Cut-On Current	I <sub>CBO</sub>	_	-10	μΑ	$V_{CB} = -50V, I_E = 0, T_A = +125^{\circ}C$
Collector Cut-Off Current	ICEX		-50	nA	$V_{CE} = -30V$ , $V_{EB(OFF)} = -0.5V$
Base Cut-Off Current	$I_{BL}$	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$
ON CHARACTERISTICS					
		75	_		$I_C = -100\mu A, V_{CE} = -10V$
		100	_		$I_C = -1.0 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain ( Note 7)	h <sub>FE</sub>	100	_	_	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		100	300		$I_C = -150 \text{mA}, V_{CE} = -10 \text{V}$
		50	_		$I_C = -500 \text{mA}, V_{CE} = -10 \text{V}$
Collector-Emitter Saturation Voltage ( Note 7)	V05(04T)		-0.4	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$
Oblicator Emiliar Oditiration Voltage (Note 1)	V <sub>CE</sub> (SAT)		-1.6		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage ( Note 7)	V <sub>BE(SAT)</sub>	_	-1.3 -2.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$
<b>3</b> ( , ,	V BE(SAT)				$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	_	8.0	pF	$V_{CB} = -10V$ , $f = 1MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>	_	30	pF	$V_{EB} = -2V, f = 1MHz, I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t <sub>off</sub>	t <sub>off</sub> — 45 ns		V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA,	
Delay Time	t <sub>d</sub>	_	10	ns	$I_{B1} = -15$ mA
Rise Time	t <sub>r</sub>		40	ns	IRI - IOIIIV
Turn-Off Time	t <sub>off</sub>		100	ns	$V_{CC} = -6V$ , $I_{C} = -150$ mA,
Storage Time	ts	_	80	ns	$I_{B1} = I_{B2} = -15$ mA
Fall Time	t <sub>f</sub>		30	ns	IB1 - IB2 - TOITIA

Note: 7. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$ 2%.



# $\textbf{Typical Electrical Characteristics} \ (@T_{A} = +25^{\circ}C, \ unless \ otherwise \ specified.)$

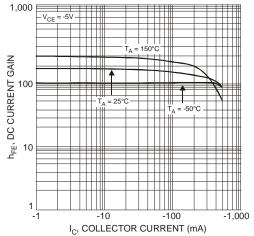
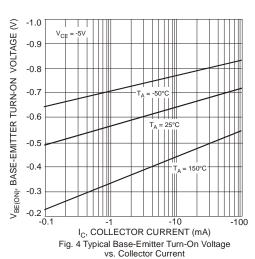


Fig. 2 Typical DC Current Gain vs. Collector Current



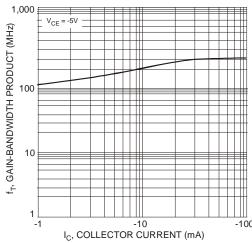


Fig. 6 Typical Gain-Bandwidth Product vs. Collector Current

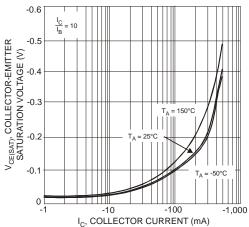
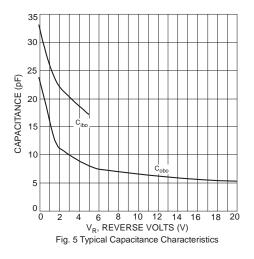


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current



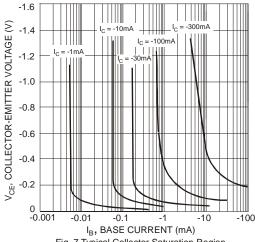
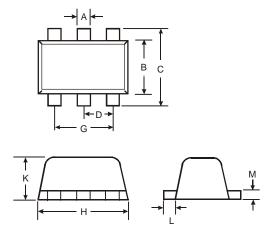


Fig. 7 Typical Collector Saturation Region



## **Package Outline Dimensions**

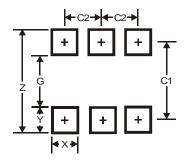
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT- 563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All	All Dimensions in mm						

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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